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### **Understanding Embedded - FPGAs (Field Programmable Gate Array)**

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### **Details**

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	6144
Total RAM Bits	36864
Number of I/O	97
Number of Gates	250000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	144-LBGA
Supplier Device Package	144-FPBGA (13x13)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/m1agl250v2-fg144">https://www.e-xfl.com/product-detail/microchip-technology/m1agl250v2-fg144</a>

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# 1 – IGLOO Device Family Overview

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## General Description

The IGLOO family of flash FPGAs, based on a 130-nm flash process, offers the lowest power FPGA, a single-chip solution, small footprint packages, reprogrammability, and an abundance of advanced features.

The Flash\*Freeze technology used in IGLOO devices enables entering and exiting an ultra-low power mode that consumes as little as 5  $\mu$ W while retaining SRAM and register data. Flash\*Freeze technology simplifies power management through I/O and clock management with rapid recovery to operation mode.

The Low Power Active capability (static idle) allows for ultra-low power consumption (from 12  $\mu$ W) while the IGLOO device is completely functional in the system. This allows the IGLOO device to control system power management based on external inputs (e.g., scanning for keyboard stimulus) while consuming minimal power.

Nonvolatile flash technology gives IGLOO devices the advantage of being a secure, low power, single-chip solution that is Instant On. IGLOO is reprogrammable and offers time-to-market benefits at an ASIC-level unit cost.

These features enable designers to create high-density systems using existing ASIC or FPGA design flows and tools.

IGLOO devices offer 1 kbit of on-chip, reprogrammable, nonvolatile FlashROM storage as well as clock conditioning circuitry based on an integrated phase-locked loop (PLL). The AGL015 and AGL030 devices have no PLL or RAM support. IGLOO devices have up to 1 million system gates, supported with up to 144 kbits of true dual-port SRAM and up to 300 user I/Os.

M1 IGLOO devices support the high-performance, 32-bit Cortex-M1 processor developed by ARM for implementation in FPGAs. Cortex-M1 is a soft processor that is fully implemented in the FPGA fabric. It has a three-stage pipeline that offers a good balance between low power consumption and speed when implemented in an M1 IGLOO device. The processor runs the ARMv6-M instruction set, has a configurable nested interrupt controller, and can be implemented with or without the debug block. Cortex-M1 is available for free from Microsemi for use in M1 IGLOO FPGAs.

The ARM-enabled devices have ordering numbers that begin with M1AGL and do not support AES decryption.

## Flash\*Freeze Technology

The IGLOO device offers unique Flash\*Freeze technology, allowing the device to enter and exit ultra-low power Flash\*Freeze mode. IGLOO devices do not need additional components to turn off I/Os or clocks while retaining the design information, SRAM content, and registers. Flash\*Freeze technology is combined with in-system programmability, which enables users to quickly and easily upgrade and update their designs in the final stages of manufacturing or in the field. The ability of IGLOO V2 devices to support a wide range of core voltage (1.2 V to 1.5 V) allows further reduction in power consumption, thus achieving the lowest total system power.

When the IGLOO device enters Flash\*Freeze mode, the device automatically shuts off the clocks and inputs to the FPGA core; when the device exits Flash\*Freeze mode, all activity resumes and data is retained.

The availability of low power modes, combined with reprogrammability, a single-chip and single-voltage solution, and availability of small-footprint, high pin-count packages, make IGLOO devices the best fit for portable electronics.

## Wide Range I/O Support

IGLOO devices support JEDEC-defined wide range I/O operation. IGLOO devices support both the JESD8-B specification, covering 3 V and 3.3 V supplies, for an effective operating range of 2.7 V to 3.6 V, and JESD8-12 with its 1.2 V nominal, supporting an effective operating range of 1.14 V to 1.575 V.

Wider I/O range means designers can eliminate power supplies or power conditioning components from the board or move to less costly components with greater tolerances. Wide range eases I/O bank management and provides enhanced protection from system voltage spikes, while providing the flexibility to easily run custom voltage applications.

## Specifying I/O States During Programming

You can modify the I/O states during programming in FlashPro. In FlashPro, this feature is supported for PDB files generated from Designer v8.5 or greater. See the *FlashPro User Guide* for more information.

Note: PDB files generated from Designer v8.1 to Designer v8.4 (including all service packs) have limited display of Pin Numbers only.

1. Load a PDB from the FlashPro GUI. You must have a PDB loaded to modify the I/O states during programming.
2. From the FlashPro GUI, click PDB Configuration. A FlashPoint – Programming File Generator window appears.
3. Click the Specify I/O States During Programming button to display the Specify I/O States During Programming dialog box.
4. Sort the pins as desired by clicking any of the column headers to sort the entries by that header. Select the I/Os you wish to modify (Figure 1-5 on page 1-9).
5. Set the I/O Output State. You can set Basic I/O settings if you want to use the default I/O settings for your pins, or use Custom I/O settings to customize the settings for each pin. Basic I/O state settings:
  - 1 – I/O is set to drive out logic High
  - 0 – I/O is set to drive out logic Low
  - Last Known State – I/O is set to the last value that was driven out prior to entering the programming mode, and then held at that value during programming
  - Z -Tri-State: I/O is tristated

**Table 2-10 • Quiescent Supply Current (IDD) Characteristics, IGLOO Sleep Mode\***

	Core Voltage	AGL015	AGL030	AGL060	AGL125	AGL250	AGL400	AGL600	AGL1000	Units
VCCI/VJTAG = 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	1.7	1.7	1.7	1.7	1.7	1.7	μA
VCCI/VJTAG = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	μA
VCCI/VJTAG = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	1.9	1.9	1.9	1.9	1.9	1.9	μA
VCCI/VJTAG = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	μA
VCCI/VJTAG = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	2.5	2.5	2.5	2.5	2.5	2.5	μA

Note:  $IDD = N_{BANKS} \times ICCI$ . Values do not include I/O static contribution, which is shown in Table 2-13 on page 2-10 through Table 2-15 on page 2-11 and Table 2-16 on page 2-11 through Table 2-18 on page 2-12 (PDC6 and PDC7).

**Table 2-11 • Quiescent Supply Current (IDD) Characteristics, IGLOO Shutdown Mode**

	Core Voltage	AGL015	AGL030	Units
Typical (25°C)	1.2 V / 1.5 V	0	0	μA

**Table 2-12 • Quiescent Supply Current (IDD), No IGLOO Flash\*Freeze Mode<sup>1</sup>**

	Core Voltage	AGL015	AGL030	AGL060	AGL125	AGL250	AGL400	AGL600	AGL1000	Units
<b>ICCA Current<sup>2</sup></b>										
Typical (25°C)	1.2 V	5	6	10	13	18	25	28	42	μA
	1.5 V	14	16	20	28	44	66	82	137	μA
<b>ICCI or IJTAG Current<sup>3</sup></b>										
VCCI/VJTAG = 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	1.7	1.7	1.7	1.7	1.7	1.7	μA
VCCI/VJTAG = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	μA
VCCI/VJTAG = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	1.9	1.9	1.9	1.9	1.9	1.9	μA
VCCI/VJTAG = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	μA
VCCI/VJTAG = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	2.5	2.5	2.5	2.5	2.5	2.5	μA

Notes:

1.  $IDD = N_{BANKS} \times ICCI + ICCA$ . JTAG counts as one bank when powered.
2. Includes VCC, VPUMP, and VCCPLL currents.
3. Values do not include I/O static contribution (PDC6 and PDC7).

## Power Consumption of Various Internal Resources

**Table 2-19 • Different Components Contributing to Dynamic Power Consumption in IGLOO Devices For IGLOO V2 or V5 Devices, 1.5 V DC Core Supply Voltage**

Parameter	Definition	Device Specific Dynamic Power (μW/MHz)							
		AGL1000	AGL600	AGL400	AGL250	AGL125	AGL060	AGL030	AGL015
PAC1	Clock contribution of a Global Rib	7.778	6.221	6.082	4.460	4.446	2.736	0.000	0.000
PAC2	Clock contribution of a Global Spine	4.334	3.512	2.759	2.718	1.753	1.971	3.483	3.483
PAC3	Clock contribution of a VersaTile row	1.379	1.445	1.377	1.483	1.467	1.503	1.472	1.472
PAC4	Clock contribution of a VersaTile used as a sequential module	0.151	0.149	0.151	0.149	0.149	0.151	0.146	0.146
PAC5	First contribution of a VersaTile used as a sequential module	0.057							
PAC6	Second contribution of a VersaTile used as a sequential module	0.207							
PAC7	Contribution of a VersaTile used as a combinatorial module	0.276	0.262	0.279	0.277	0.280	0.300	0.281	0.273
PAC8	Average contribution of a routing net	1.161	1.147	1.193	1.273	1.076	1.088	1.134	1.153
PAC9	Contribution of an I/O input pin (standard-dependent)	See Table 2-13 on page 2-10 through Table 2-15 on page 2-11.							
PAC10	Contribution of an I/O output pin (standard-dependent)	See Table 2-16 on page 2-11 through Table 2-18 on page 2-12.							
PAC11	Average contribution of a RAM block during a read operation	25.00							
PAC12	Average contribution of a RAM block during a write operation	30.00							
PAC13	Dynamic PLL contribution	2.70							

Note: For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or SmartPower tool in Libero SoC.

**Table 2-20 • Different Components Contributing to the Static Power Consumption in IGLOO Devices  
For IGLOO V2 or V5 Devices, 1.5 V DC Core Supply Voltage**

Parameter	Definition	Device-Specific Static Power (mW)							
		AGL1000	AGL600	AGL400	AGL250	AGL125	AGL060	AGL030	AGL015
PDC1	Array static power in Active mode	See Table 2-12 on page 2-9.							
PDC2	Array static power in Static (Idle) mode	See Table 2-11 on page 2-8.							
PDC3	Array static power in Flash*Freeze mode	See Table 2-9 on page 2-7.							
PDC4	Static PLL contribution	1.84							
PDC5	Bank quiescent power ( $V_{CC1}$ -dependent)	See Table 2-12 on page 2-9.							
PDC6	I/O input pin static power (standard-dependent)	See Table 2-13 on page 2-10 through Table 2-15 on page 2-11.							
PDC7	I/O output pin static power (standard-dependent)	See Table 2-16 on page 2-11 through Table 2-18 on page 2-12.							

Note: \*For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or SmartPower tool in Libero SoC.

**Combinatorial Cells Contribution— $P_{C-CELL}$** 

$$P_{C-CELL} = N_{C-CELL} * \alpha_1 / 2 * P_{AC7} * F_{CLK}$$

$N_{C-CELL}$  is the number of VersaTiles used as combinatorial modules in the design.

$\alpha_1$  is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-23 on page 2-19.

$F_{CLK}$  is the global clock signal frequency.

**Routing Net Contribution— $P_{NET}$** 

$$P_{NET} = (N_{S-CELL} + N_{C-CELL}) * \alpha_1 / 2 * P_{AC8} * F_{CLK}$$

$N_{S-CELL}$  is the number of VersaTiles used as sequential modules in the design.

$N_{C-CELL}$  is the number of VersaTiles used as combinatorial modules in the design.

$\alpha_1$  is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-23 on page 2-19.

$F_{CLK}$  is the global clock signal frequency.

**I/O Input Buffer Contribution— $P_{INPUTS}$** 

$$P_{INPUTS} = N_{INPUTS} * \alpha_2 / 2 * P_{AC9} * F_{CLK}$$

$N_{INPUTS}$  is the number of I/O input buffers used in the design.

$\alpha_2$  is the I/O buffer toggle rate—guidelines are provided in Table 2-23 on page 2-19.

$F_{CLK}$  is the global clock signal frequency.

**I/O Output Buffer Contribution— $P_{OUTPUTS}$** 

$$P_{OUTPUTS} = N_{OUTPUTS} * \alpha_2 / 2 * \beta_1 * P_{AC10} * F_{CLK}$$

$N_{OUTPUTS}$  is the number of I/O output buffers used in the design.

$\alpha_2$  is the I/O buffer toggle rate—guidelines are provided in Table 2-23 on page 2-19.

$\beta_1$  is the I/O buffer enable rate—guidelines are provided in Table 2-24 on page 2-19.

$F_{CLK}$  is the global clock signal frequency.

**RAM Contribution— $P_{MEMORY}$** 

$$P_{MEMORY} = P_{AC11} * N_{BLOCKS} * F_{READ-CLOCK} * \beta_2 + P_{AC12} * N_{BLOCK} * F_{WRITE-CLOCK} * \beta_3$$

$N_{BLOCKS}$  is the number of RAM blocks used in the design.

$F_{READ-CLOCK}$  is the memory read clock frequency.

$\beta_2$  is the RAM enable rate for read operations.

$F_{WRITE-CLOCK}$  is the memory write clock frequency.

$\beta_3$  is the RAM enable rate for write operations—guidelines are provided in Table 2-24 on page 2-19.

**PLL Contribution— $P_{PLL}$** 

$$P_{PLL} = P_{DC4} + P_{AC13} * F_{CLKOUT}$$

$F_{CLKOUT}$  is the output clock frequency.†

† If a PLL is used to generate more than one output clock, include each output clock in the formula by adding its corresponding contribution ( $P_{AC13} * F_{CLKOUT}$  product) to the total PLL contribution.

**Table 2-33 • Summary of I/O Timing Characteristics—Software Default Settings, Std. Speed Grade, Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$ , Worst-Case  $V_{CCI}$  (per standard) Applicable to Standard I/O Banks**

I/O Standard	Drive Strength)	Equivalent Software Default Drive Strength Option <sup>1</sup> (mA)	Slew Rate	Capacitive Load (pF)	External Resistor ( $\Omega$ )	$t_{DOUT}$ (ns)	$t_{DP}$ (ns)	$t_{DIN}$ (ns)	$t_{PY}$ (ns)	$t_{EOUT}$ (ns)	$t_{ZL}$ (ns)	$t_{ZH}$ (ns)	$t_{LZ}$ (ns)	$t_{HZ}$ (ns)	Units
3.3 V LVTTTL / 3.3 V LVCMOS	8 mA	8	High	5	–	0.97	1.85	0.18	0.83	0.66	1.89	1.46	1.96	2.26	ns
3.3 V LVCMOS Wide Range <sup>2</sup>	100 $\mu\text{A}$	8	High	5	–	0.97	2.62	0.18	1.17	0.66	2.63	2.02	2.79	3.17	ns
2.5 V LVCMOS	8 mA	8	High	5	–	0.97	1.88	0.18	1.04	0.66	1.92	1.63	1.95	2.15	ns
1.8 V LVCMOS	4 mA	4	High	5	–	0.97	2.18	0.18	0.98	0.66	2.22	1.93	1.97	2.06	ns
1.5 V LVCMOS	2 mA	2	High	5	–	0.97	2.51	0.18	1.14	0.66	2.56	2.21	1.99	2.03	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is  $\pm 100\ \mu\text{A}$ . Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

## Detailed I/O DC Characteristics

**Table 2-37 • Input Capacitance**

Symbol	Definition	Conditions	Min.	Max.	Units
C <sub>IN</sub>	Input capacitance	V <sub>IN</sub> = 0, f = 1.0 MHz		8	pF
C <sub>INCLK</sub>	Input capacitance on the clock pin	V <sub>IN</sub> = 0, f = 1.0 MHz		8	pF

**Table 2-38 • I/O Output Buffer Maximum Resistances<sup>1</sup>  
Applicable to Advanced I/O Banks**

Standard	Drive Strength	R <sub>PULL-DOWN</sub> (Ω) <sup>2</sup>	R <sub>PULL-UP</sub> (Ω) <sup>3</sup>
3.3 V LVTTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	17	50
	24 mA	11	33
3.3 V LVCMOS Wide Range	100 μA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
	16 mA	20	40
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
	6 mA	67	75
	8 mA	33	37
	12 mA	33	37
1.2 V LVCMOS <sup>4</sup>	2 mA	158	164
1.2 V LVCMOS Wide Range <sup>4</sup>	100 μA	Same as regular 1.2 V LVCMOS	Same as regular 1.2 V LVCMOS
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75

Notes:

1. These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located at <http://www.microsemi.com/soc/download/ibis/default.aspx>.
2.  $R_{(PULL-DOWN-MAX)} = (VOL_{spec}) / I_{OL_{spec}}$
3.  $R_{(PULL-UP-MAX)} = (VCCI_{max} - VOH_{spec}) / I_{OH_{spec}}$
4. Applicable to IGLOO V2 Devices operating at  $VCCI \geq VCC$

## Single-Ended I/O Characteristics

### 3.3 V LVTTTL / 3.3 V LVCMOS

Low-Voltage Transistor–Transistor Logic (LVTTTL) is a general-purpose standard (EIA/JESD) for 3.3 V applications. It uses an LVTTTL input buffer and push-pull output buffer. Furthermore, all LVCMOS 3.3 V software macros comply with LVCMOS 3.3 V wide range as specified in the JESD8a specification.

**Table 2-47 • Minimum and Maximum DC Input and Output Levels**  
Applicable to Advanced I/O Banks

3.3 V LVTTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL <sup>1</sup>	IIH <sup>2</sup>
	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA <sup>3</sup>	Max. mA <sup>3</sup>	μA <sup>4</sup>	μA <sup>4</sup>
2 mA	-0.3	0.8	2	3.6	0.4	2.4	2	2	25	27	10	10
4 mA	-0.3	0.8	2	3.6	0.4	2.4	4	4	25	27	10	10
6 mA	-0.3	0.8	2	3.6	0.4	2.4	6	6	51	54	10	10
8 mA	-0.3	0.8	2	3.6	0.4	2.4	8	8	51	54	10	10
12 mA	-0.3	0.8	2	3.6	0.4	2.4	12	12	103	109	10	10
16 mA	-0.3	0.8	2	3.6	0.4	2.4	16	16	132	127	10	10
24 mA	-0.3	0.8	2	3.6	0.4	2.4	24	24	268	181	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where  $-0.3\text{ V} < V_{IN} < V_{IL}$ .
2. IIH is the input leakage current per I/O pin over recommended operating conditions  $V_{IH} < V_{IN} < V_{CCI}$ . Input current is larger when operating outside recommended ranges.
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

**Table 2-48 • Minimum and Maximum DC Input and Output Levels**  
Applicable to Standard Plus I/O Banks

3.3 V LVTTTL / 3.3 V LVCMOS	VIL		VIH		V <sub>OL</sub>	VOH	IOL	IOH	IOSL	IOSH	IIL <sup>1</sup>	IIH <sup>2</sup>
	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA <sup>3</sup>	Max. mA <sup>3</sup>	μA <sup>4</sup>	μA <sup>4</sup>
2 mA	-0.3	0.8	2	3.6	0.4	2.4	2	2	25	27	10	10
4 mA	-0.3	0.8	2	3.6	0.4	2.4	4	4	25	27	10	10
6 mA	-0.3	0.8	2	3.6	0.4	2.4	6	6	51	54	10	10
8 mA	-0.3	0.8	2	3.6	0.4	2.4	8	8	51	54	10	10
12 mA	-0.3	0.8	2	3.6	0.4	2.4	12	12	103	109	10	10
16 mA	-0.3	0.8	2	3.6	0.4	2.4	16	16	103	109	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where  $-0.3\text{ V} < V_{IN} < V_{IL}$ .
2. IIH is the input leakage current per I/O pin over recommended operating conditions  $V_{IH} < V_{IN} < V_{CCI}$ . Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

**Table 2-104 • 1.8 V LVC MOS High Slew – Applies to 1.5 V DC Core Voltage**  
**Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V**  
**Applicable to Standard Banks**

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	Units
2 mA	Std.	2.62	0.18	0.98	0.66	2.67	2.59	1.67	1.29	2.62	ns
4 mA	Std.	2.18	0.18	0.98	0.66	2.22	1.93	1.97	2.06	2.18	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

**1.2 V DC Core Voltage**

**Table 2-105 • 1.8 V LVC MOS Low Slew – Applies to 1.2 V DC Core Voltage**  
**Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V**  
**Applicable to Advanced I/O Banks**

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
2 mA	Std.	1.55	6.97	0.26	1.11	1.10	7.08	6.48	2.87	2.29	12.87	12.27	ns
4 mA	Std.	1.55	5.91	0.26	1.11	1.10	6.01	5.57	3.21	3.14	11.79	11.36	ns
6 mA	Std.	1.55	5.16	0.26	1.11	1.10	5.24	4.95	3.45	3.55	11.03	10.74	ns
8 mA	Std.	1.55	4.90	0.26	1.11	1.10	4.98	4.81	3.50	3.66	10.77	10.60	ns
12 mA	Std.	1.55	4.83	0.26	1.11	1.10	4.90	4.83	3.58	4.08	10.68	10.61	ns
16 mA	Std.	1.55	4.83	0.26	1.11	1.10	4.90	4.83	3.58	4.08	10.68	10.61	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

**Table 2-106 • 1.8 V LVC MOS High Slew – Applies to 1.2 V DC Core Voltage**  
**Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V**  
**Applicable to Advanced I/O Banks**

Drive Strength	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	$t_{ZLS}$	$t_{ZHS}$	Units
2 mA	Std.	1.55	3.73	0.26	1.11	1.10	3.71	3.73	2.86	2.34	9.49	9.51	ns
4 mA	Std.	1.55	3.12	0.26	1.11	1.10	3.16	2.97	3.21	3.22	8.95	8.75	ns
6 mA	Std.	1.55	2.79	0.26	1.11	1.10	2.83	2.59	3.45	3.65	8.62	8.38	ns
8 mA	Std.	1.55	2.73	0.26	1.11	1.10	2.77	2.52	3.50	3.75	8.56	8.30	ns
12 mA	Std.	1.55	2.72	0.26	1.11	1.10	2.76	2.43	3.58	4.19	8.55	8.22	ns
16 mA	Std.	1.55	2.72	0.26	1.11	1.10	2.76	2.43	3.58	4.19	8.55	8.22	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

## Output Enable Register

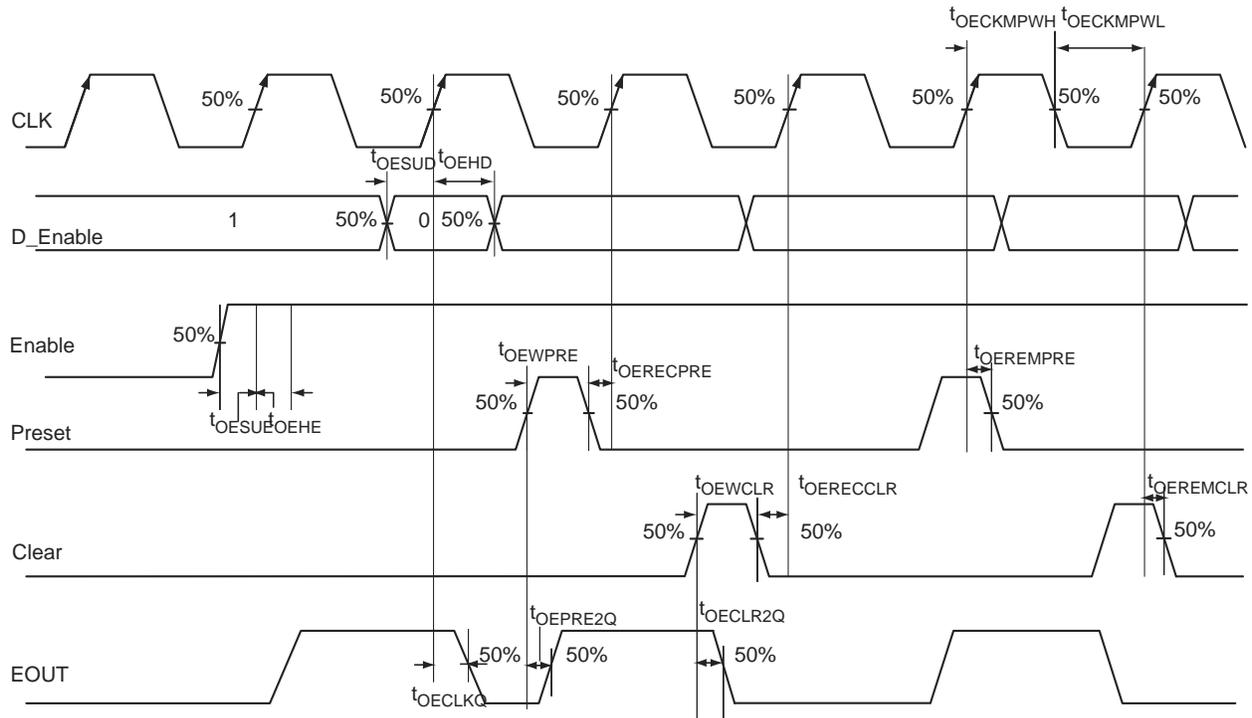


Figure 2-20 • Output Enable Register Timing Diagram

### Timing Characteristics

1.5 V DC Core Voltage

Table 2-161 • Output Enable Register Propagation Delays

Commercial-Case Conditions:  $T_j = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
$t_{OECLKQ}$	Clock-to-Q of the Output Enable Register	0.75	ns
$t_{OESUD}$	Data Setup Time for the Output Enable Register	0.51	ns
$t_{OEHD}$	Data Hold Time for the Output Enable Register	0.00	ns
$t_{OESUE}$	Enable Setup Time for the Output Enable Register	0.73	ns
$t_{OEHE}$	Enable Hold Time for the Output Enable Register	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	1.13	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	1.13	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	ns
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.24	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	ns
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.24	ns
$t_{OEWCLR}$	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.19	ns
$t_{OEWPRE}$	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.19	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.31	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

## 1.2 V DC Core Voltage

Table 2-165 • Input DDR Propagation Delays

Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.14\text{ V}$ 

Parameter	Description	Std.	Units
$t_{\text{DDRICKLQ1}}$	Clock-to-Out Out_QR for Input DDR	0.76	ns
$t_{\text{DDRICKLQ2}}$	Clock-to-Out Out_QF for Input DDR	0.94	ns
$t_{\text{DDRISUD1}}$	Data Setup for Input DDR (negedge)	0.93	ns
$t_{\text{DDRISUD2}}$	Data Setup for Input DDR (posedge)	0.84	ns
$t_{\text{DDRILD1}}$	Data Hold for Input DDR (negedge)	0.00	ns
$t_{\text{DDRILD2}}$	Data Hold for Input DDR (posedge)	0.00	ns
$t_{\text{DDRICLR2Q1}}$	Asynchronous Clear-to-Out Out_QR for Input DDR	1.23	ns
$t_{\text{DDRICLR2Q2}}$	Asynchronous Clear-to-Out Out_QF for Input DDR	1.42	ns
$t_{\text{DDRIREMCLR}}$	Asynchronous Clear Removal Time for Input DDR	0.00	ns
$t_{\text{DDRIRECCLR}}$	Asynchronous Clear Recovery Time for Input DDR	0.24	ns
$t_{\text{DDRIWCLR}}$	Asynchronous Clear Minimum Pulse Width for Input DDR	0.19	ns
$t_{\text{DDRICKMPWH}}$	Clock Minimum Pulse Width High for Input DDR	0.31	ns
$t_{\text{DDRICKMPWL}}$	Clock Minimum Pulse Width Low for Input DDR	0.28	ns
$F_{\text{DDRIMAX}}$	Maximum Frequency for Input DDR	160.00	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

CS196	
Pin Number	AGL400 Function
A1	GND
A2	GAA0/IO00RSB0
A3	GAC0/IO04RSB0
A4	GAC1/IO05RSB0
A5	IO14RSB0
A6	IO18RSB0
A7	IO26RSB0
A8	IO29RSB0
A9	IO36RSB0
A10	GBC0/IO54RSB0
A11	GBB0/IO56RSB0
A12	GBB1/IO57RSB0
A13	GBA1/IO59RSB0
A14	GND
B1	VCCIB3
B2	VMV0
B2	VMV0
B3	GAA1/IO01RSB0
B4	GAB1/IO03RSB0
B5	GND
B6	IO17RSB0
B7	IO25RSB0
B8	IO34RSB0
B9	IO39RSB0
B10	GND
B11	GBC1/IO55RSB0
B12	GBA0/IO58RSB0
B13	GBA2/IO60PPB1
B14	GBB2/IO61PDB1
C1	GAC2/IO153UDB3
C2	GAB2/IO154UDB3
C3	GNDQ
C4	VCCIB0
C5	GAB0/IO02RSB0
C6	IO15RSB0
C7	VCCIB0

CS196	
Pin Number	AGL400 Function
C8	IO31RSB0
C9	IO44RSB0
C10	IO49RSB0
C11	VCCIB0
C12	IO60NPB1
C13	GNDQ
C14	IO61NDB1
D1	IO153VDB3
D2	IO154VDB3
D3	GAA2/IO155UDB3
D4	IO150PPB3
D5	IO11RSB0
D6	IO20RSB0
D7	IO23RSB0
D8	IO28RSB0
D9	IO41RSB0
D10	IO47RSB0
D11	IO63PPB1
D12	VMV1
D13	IO62NDB1
D14	GBC2/IO62PDB1
E1	IO149PDB3
E2	GND
E3	IO155VDB3
E4	VCCIB3
E5	IO151USB3
E6	IO09RSB0
E7	IO12RSB0
E8	IO32RSB0
E9	IO46RSB0
E10	IO51RSB0
E11	VCCIB1
E12	IO63NPB1
E13	GND
E14	IO64PDB1
F1	IO149NDB3

CS196	
Pin Number	AGL400 Function
F2	IO144NPB3
F3	IO148PDB3
F4	IO148NDB3
F5	IO150NPB3
F6	IO07RSB0
F7	VCC
F8	VCC
F9	IO43RSB0
F10	IO73PDB1
F11	IO73NDB1
F12	IO66NDB1
F13	IO66PDB1
F14	IO64NDB1
G1	GFB1/IO146PDB3
G2	GFA0/IO145NDB3
G3	GFA2/IO144PPB3
G4	VCOMPLF
G5	GFC0/IO147NDB3
G6	VCC
G7	GND
G8	GND
G9	VCC
G10	GCC0/IO67NDB1
G11	GCB1/IO68PDB1
G12	GCA0/IO69NDB1
G13	IO72NDB1
G14	GCC2/IO72PDB1
H1	GFB0/IO146NDB3
H2	GFA1/IO145PDB3
H3	VCCPLF
H4	GFB2/IO143PPB3
H5	GFC1/IO147PDB3
H6	VCC
H7	GND
H8	GND
H9	VCC

QN48	
Pin Number	AGL030 Function
1	IO82RSB1
2	GEC0/IO73RSB1
3	GEA0/IO72RSB1
4	GEB0/IO71RSB1
5	GND
6	VCCIB1
7	IO68RSB1
8	IO67RSB1
9	IO66RSB1
10	IO65RSB1
11	IO64RSB1
12	IO62RSB1
13	IO61RSB1
14	FF/IO60RSB1
15	IO57RSB1
16	IO55RSB1
17	IO53RSB1
18	VCC
19	VCCIB1
20	IO46RSB1
21	IO42RSB1
22	TCK
23	TDI
24	TMS
25	VPUMP
26	TDO
27	TRST
28	VJTAG
29	IO38RSB0
30	GDB0/IO34RSB0
31	GDA0/IO33RSB0
32	GDC0/IO32RSB0
33	VCCIB0
34	GND
35	VCC
36	IO25RSB0

QN48	
Pin Number	AGL030 Function
37	IO24RSB0
38	IO22RSB0
39	IO20RSB0
40	IO18RSB0
41	IO16RSB0
42	IO14RSB0
43	IO10RSB0
44	IO08RSB0
45	IO06RSB0
46	IO04RSB0
47	IO02RSB0
48	IO00RSB0

<b>FG144</b>	
<b>Pin Number</b>	<b>AGL250 Function</b>
K1	GEB0/IO99NDB3
K2	GEA1/IO98PDB3
K3	GEA0/IO98NDB3
K4	GEA2/IO97RSB2
K5	IO90RSB2
K6	IO84RSB2
K7	GND
K8	IO66RSB2
K9	GDC2/IO63RSB2
K10	GND
K11	GDA0/IO60VDB1
K12	GDB0/IO59VDB1
L1	GND
L2	VMV3
L3	FF/GEB2/IO96RSB2
L4	IO91RSB2
L5	VCCIB2
L6	IO82RSB2
L7	IO80RSB2
L8	IO72RSB2
L9	TMS
L10	VJTAG
L11	VMV2
L12	TRST
M1	GNDQ
M2	GEC2/IO95RSB2
M3	IO92RSB2
M4	IO89RSB2
M5	IO87RSB2
M6	IO85RSB2
M7	IO78RSB2
M8	IO76RSB2
M9	TDI
M10	VCCIB2
M11	VPUMP
M12	GNDQ

<b>FG484</b>	
<b>Pin Number</b>	<b>AGL400 Function</b>
C21	NC
C22	VCCIB1
D1	NC
D2	NC
D3	NC
D4	GND
D5	GAA0/IO00RSB0
D6	GAA1/IO01RSB0
D7	GAB0/IO02RSB0
D8	IO16RSB0
D9	IO17RSB0
D10	IO22RSB0
D11	IO28RSB0
D12	IO34RSB0
D13	IO37RSB0
D14	IO41RSB0
D15	IO43RSB0
D16	GBB1/IO57RSB0
D17	GBA0/IO58RSB0
D18	GBA1/IO59RSB0
D19	GND
D20	NC
D21	NC
D22	NC
E1	NC
E2	NC
E3	GND
E4	GAB2/IO154UDB3
E5	GAA2/IO155UDB3
E6	IO12RSB0
E7	GAB1/IO03RSB0
E8	IO13RSB0
E9	IO14RSB0
E10	IO21RSB0
E11	IO27RSB0
E12	IO32RSB0

FG484	
Pin Number	AGL600 Function
G5	IO171PDB3
G6	GAC2/IO172PDB3
G7	IO06RSB0
G8	GNDQ
G9	IO10RSB0
G10	IO19RSB0
G11	IO26RSB0
G12	IO30RSB0
G13	IO40RSB0
G14	IO45RSB0
G15	GNDQ
G16	IO50RSB0
G17	GBB2/IO61PPB1
G18	IO53RSB0
G19	IO63NDB1
G20	NC
G21	NC
G22	NC
H1	NC
H2	NC
H3	VCC
H4	IO166PDB3
H5	IO167NPB3
H6	IO172NDB3
H7	IO169NDB3
H8	VMV0
H9	VCCIB0
H10	VCCIB0
H11	IO25RSB0
H12	IO31RSB0
H13	VCCIB0
H14	VCCIB0
H15	VMV1
H16	GBC2/IO62PDB1
H17	IO67PPB1
H18	IO64PPB1

FG484	
Pin Number	AGL600 Function
N17	IO80NPB1
N18	IO74NPB1
N19	IO72NDB1
N20	NC
N21	IO79NPB1
N22	NC
P1	NC
P2	IO153PDB3
P3	IO153NDB3
P4	IO159NDB3
P5	IO156NPB3
P6	IO151PPB3
P7	IO158PPB3
P8	VCCIB3
P9	GND
P10	VCC
P11	VCC
P12	VCC
P13	VCC
P14	GND
P15	VCCIB1
P16	GDB0/IO87NPB1
P17	IO85NDB1
P18	IO85PDB1
P19	IO84PDB1
P20	NC
P21	IO81PDB1
P22	NC
R1	NC
R2	NC
R3	VCC
R4	IO150PDB3
R5	IO151NPB3
R6	IO147NPB3
R7	GEC0/IO146NPB3
R8	VMV3

<b>FG484</b>	
<b>Pin Number</b>	<b>AGL1000 Function</b>
N17	IO100NPB1
N18	IO102NDB1
N19	IO102PDB1
N20	NC
N21	IO101NPB1
N22	IO103PDB1
P1	NC
P2	IO199PDB3
P3	IO199NDB3
P4	IO202NDB3
P5	IO202PDB3
P6	IO196PPB3
P7	IO193PPB3
P8	VCCIB3
P9	GND
P10	VCC
P11	VCC
P12	VCC
P13	VCC
P14	GND
P15	VCCIB1
P16	GDB0/IO112NPB1
P17	IO106NDB1
P18	IO106PDB1
P19	IO107PDB1
P20	NC
P21	IO104PDB1
P22	IO103NDB1
R1	NC
R2	IO197PPB3
R3	VCC
R4	IO197NPB3
R5	IO196NPB3
R6	IO193NPB3
R7	GEC0/IO190NPB3
R8	VMV3

<b>FG484</b>	
<b>Pin Number</b>	<b>AGL1000 Function</b>
Y7	IO174RSB2
Y8	VCC
Y9	VCC
Y10	IO154RSB2
Y11	IO148RSB2
Y12	IO140RSB2
Y13	NC
Y14	VCC
Y15	VCC
Y16	NC
Y17	NC
Y18	GND
Y19	NC
Y20	NC
Y21	NC
Y22	VCCIB1